

Quad 2-Input Multiplexer

Features

- Function, pinout, and drive compatible with FCT and F logic
- FCT-C speed at 4.3 ns max. (Com'l)
FCT-A speed at 5.0 ns max. (Com'l)
- Reduced V_{OH} (typically $\approx 3.3V$) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- Power-off disable feature
- Matched rise and fall times
- Fully compatible with TTL input and output logic levels
- ESD > 2000V

- Sink current 64 mA (Com'l),
32 mA (Mil)
- Source current 32 mA (Com'l),
12 mA (Mil)

Functional Description

The FCT257T has four identical two-input multiplexers which select four bits of data from two sources under the control of a common data Select input (S). The I_0 inputs are selected when the Select input is LOW and the I_1 inputs are selected when the Select input is HIGH. Data appears at the output in true non-inverted form for the FCT257T.

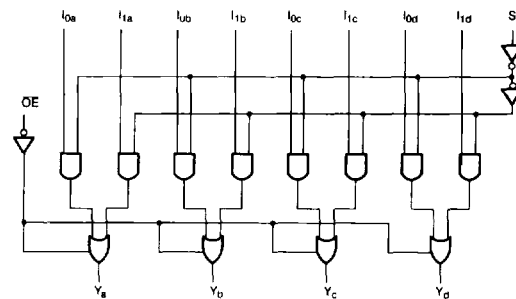
The FCT257T is a logic implementation of a four-pole, two position switch where

the position of the switch is determined by the logic levels supplied to the select input. Outputs are forced to a high-impedance "OFF" state when the Output Enable input (OE) is HIGH.

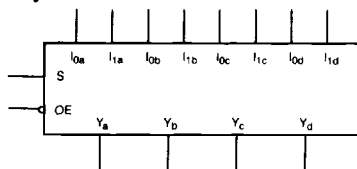
All but one device must be in the high-impedance state to avoid currents exceeding the maximum ratings if outputs are tied together. Design of the Output Enable signals must ensure that there is no overlap when outputs of three-state devices are tied together.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.

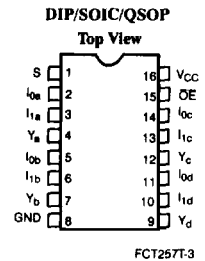
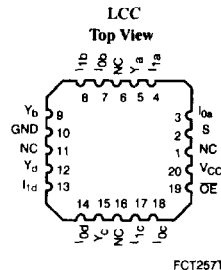
Logic Block Diagram



Logic Symbol



Pin Configurations



Pin Description

Name	Description
I	Data Inputs
S	Common Select Input
OE	Enable Inputs (Active LOW)
Y	Data Outputs

Function Table⁽¹⁾

Inputs				Output
OE	S	I ₀	I ₁	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	L	X	L
L	L	H	X	H

Note:

1. H = HIGH Voltage Level, L = LOW Voltage Level, X = Don't Care, Z = High impedance (OFF) state

Maximum Ratings^[2, 3]

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	–65°C to +150°C
Ambient Temperature with Power Applied	–65°C to +135°C
Supply Voltage to Ground Potential	–0.5V to +7.0V
DC Input Voltage	–0.5V to +7.0V
DC Output Voltage	–0.5V to +7.0V
DC Output Current (Maximum Sink Current/Pin)	120 mA
Power Dissipation	0.5W

Static Discharge Voltage >2001V
(per MIL-STD-883, Method 3015)

Operating Range

Range	Range	Ambient Temperature	V _{CC}
Commercial	CT	0°C to +70°C	5V ± 5%
Commercial	T, AT	–40°C to +85°C	5V ± 5%
Military ^[4]	All	–55°C to +125°C	5V ± 10%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	Min.	Typ. ^[5]	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{CC} =Min., I _{OH} =–32 mA	Com'l	2.0		V
		V _{CC} =Min., I _{OH} =–15 mA	Com'l	2.4	3.3	V
		V _{CC} =Min., I _{OH} =–12 mA	Mil	2.4	3.3	V
V _{OL}	Output LOW Voltage	V _{CC} =Min., I _{OL} =64 mA	Com'l		0.3	0.55 V
		V _{CC} =Min., I _{OL} =32 mA	Mil		0.3	0.55 V
V _{IH}	Input HIGH Voltage		2.0			V
V _{IL}	Input LOW Voltage				0.8	V
V _H	Hysteresis ^[6]	All inputs		0.2		V
V _{IK}	Input Clamp Diode Voltage	V _{CC} =Min., I _{IN} =–18 mA		–0.7	–1.2	V
I _I	Input HIGH Current	V _{CC} =Max., V _{IN} =V _{CC}			5	μA
I _{IH}	Input HIGH Current	V _{CC} =Max., V _{IN} =2.7V			±1	μA
I _{IL}	Input LOW Current	V _{CC} =Max., V _{IN} =0.5V			±1	μA
I _{OZH}	Off State HIGH-Level Output Current	V _{CC} =Max., V _{OUT} =2.7V			10	μA
I _{OZL}	Off State LOW-Level Output Current	V _{CC} =Max., V _{OUT} =0.5V			–10	μA
I _{OS}	Output Short Circuit Current ^[7]	V _{CC} =Max., V _{OUT} =0.0V	–60	–120	–225	mA
I _{OFF}	Power-Off Disable	V _{CC} =0V, V _{OUT} =4.5V			±1	μA

Capacitance^[6]

Parameter	Description	Typ. ^[5]	Max.	Unit
C _{IN}	Input Capacitance	5	10	pF
C _{OUT}	Output Capacitance	9	12	pF

Notes:

- Unless otherwise noted, these limits are over the operating free-air temperature range.
- Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.
- T_A is the “instant on” case temperature.
- Typical values are at V_{CC}=5.0V, T_A=+25°C ambient.
- This parameter is guaranteed but not tested.
- Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.



Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
I_{CC}	Quiescent Power Supply Current	$V_{CC} = \text{Max.}, V_{IN} \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$	0.1	0.2	mA
ΔI_{CC}	Quiescent Power Supply Current (TTL inputs HIGH)	$V_{CC} = \text{Max.}, V_{IN} = 3.4V$ ^[8] $f_1 = 0$, Outputs Open	0.5	2.0	mA
I_{CCD}	Dynamic Power Supply Current ^[9]	$V_{CC} = \text{Max.}$, One Input Toggling, 50% Duty Cycle, Outputs Open, $OE = GND$, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$	0.06	0.12	mA/ MHz
I_C	Total Power Supply Current ^[10]	$V_{CC} = \text{Max.}$, 50% Duty Cycle, Outputs Open, One Input Toggling at $f_1 = 10$ MHz, $OE = GND$, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$	0.7	1.4	mA
		$V_{CC} = \text{Max.}$, 50% Duty Cycle, Outputs Open, One Input Toggling at $f_1 = 10$ MHz, $OE = GND$, $V_{IN} = 3.4V$ or $V_{IN} = GND$	1.0	2.4	mA
		$V_{CC} = \text{Max.}$, 50% Duty Cycle, Outputs Open, Four Bits Toggling at $f_1 = 2.5$ MHz, $OE = GND$, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$	0.7	1.4 ^[11]	mA
		$V_{CC} = \text{Max.}$, 50% Duty Cycle, Outputs Open, Four Bits Toggling at $f_1 = 2.5$ MHz, $OE = GND$, $V_{IN} = 3.4V$ or $V_{IN} = GND$	1.7	5.4 ^[11]	mA

Notes:

8. Per TTL driven input ($V_{IN} = 3.4V$); all other inputs at V_{CC} or GND.
 9. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
 10. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$
 $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_0/2 + f_1 N_I)$
 I_{CC} = Quiescent Current with CMOS input levels
 ΔI_{CC} = Power Supply Current for a TTL HIGH input ($V_{IN} = 3.4V$)
 D_H = Duty Cycle for TTL inputs HIGH

N_T = Number of TTL inputs at D_H

I_{CCD} = Dynamic Current caused by an input transition pair (HLH or LHL)

f_0 = Clock frequency for registered devices, otherwise zero

f_1 = Input signal frequency

N_I = Number of inputs changing at f_1

All currents are in milliamps and all frequencies are in megahertz.

11. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

Switching Characteristics Over the Operating Range

Parameter	Description	FCT257T				FCT257AT				Unit	Fig. No.[13]
		Military		Commercial		Military		Commercial			
		Min.[12]	Max.	Min.[12]	Max.	Min.[12]	Max.	Min.[12]	Max.		
tPLH tPHL	Propagation Delay I to Y	1.5	7.0	1.5	6.0	1.5	5.8	1.5	5.0	ns	1, 3
tPLH tPHL	Propagation Delay S to O	1.5	12.0	1.5	10.5	1.5	8.1	1.5	7.0	ns	1, 3
tPZH tPZL	Output Enable Time	1.5	10.0	1.5	8.5	1.5	8.0	1.5	7.0	ns	1, 7, 8
tPHZ tPLZ	Output Disable Time	1.5	8.0	1.5	6.0	1.5	5.8	1.5	5.5	ns	1, 7, 8

Parameter	Description	FCT257CT				Unit	Fig. No.[3]
		Military		Commercial			
		Min.[12]	Max.	Min.[12]	Max.		
t _{PLH} t _{PHL}	Propagation Delay I to Y	1.5	5.0	1.5	4.3	ns	1, 3
t _{PLH} t _{PHL}	Propagation Delay S to O _n	1.5	6.0	1.5	5.2	ns	1, 3
t _{PZH} t _{PZL}	Output Enable Time	1.5	6.8	1.5	6.0	ns	1, 7, 8
t _{PHZ} t _{PLZ}	Output Disable Time	1.5	5.3	1.5	5.0	ns	1, 7, 8

Notes:

12. Minimum limits are guaranteed but not tested on Propagation Delays.
 13. See "Parameter Measurement Information" in the General Information Section.

**Ordering Information**

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
4.3	CY74FCT257CTPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT257CTQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT257CTSOC	S1	16-Lead (300-Mil) Molded SOIC	
5.0	CY54FCT257CTDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT257CTLMB	L61	20-Pin Square Leadless Chip Carrier	
5.0	CY74FCT257ATPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT257ATQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT257ATSOC	S1	16-Lead (300-Mil) Molded SOIC	
5.8	CY54FCT257ATDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT257ATLMB	L61	20-Pin Square Leadless Chip Carrier	
6.0	CY74FCT257TPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT257TQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT257TSOC	S1	16-Lead (300-Mil) Molded SOIC	
7.0	CY54FCT257TDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT257TLMB	L61	20-Pin Square Leadless Chip Carrier	

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